

What is claimed is:

1. A sprayed coating formed by plasma spraying inside a semiconductor processing device, the coating comprising:
 - a metal oxide composed of oxygen and a metal, or a semiconductor oxide composed of oxygen and a semiconductor;
 - wherein a composition ratio of the oxygen with respect to the metal or the semiconductor is not less than 80% of a composition ratio of the stoichiometric composition.
2. The sprayed coating according to claim 1, wherein the metal or the semiconductor comprises at least one of an alkaline-earth metal, a rare-earth metal, Al, Ta, and Si.
3. The sprayed coating according to claim 1, wherein the metal oxide is aluminum oxide and a percentage of actual composition ratio to stoichiometric composition ratio is not less than 85%.
4. The sprayed coating according to claim 1, wherein the metal oxide is magnesium oxide and a percentage of actual composition ratio to stoichiometric composition ratio is not less than 81%.
5. The sprayed coating according to claim 1, wherein the metal oxide is yttrium oxide and a percentage of actual composition ratio to stoichiometric composition ratio is not less than 85%.

6. A production method for a sprayed coating, comprising a step of forming a coating by plasma spraying inside a semiconductor processing device, wherein a plasma operating gas is oxygen gas or a gas including oxygen.
7. The production method for a sprayed coating according to claim 6, wherein the atmosphere in which plasma spraying is conducted is air.